

60 V, 1 A PNP/PNP low VCEsat (BISS) transistor

23 January 2013

Product data sheet

1. General description

PNP/PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package.

NPN/PNP complement: PBSS4160PANP. NPN/NPN complement: PBSS4160PAN.

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability ${\sf I}_{\sf C}$ and ${\sf I}_{\sf CM}$
- High collector current gain h_{FE} at high I_C
- Reduced Printed-Circuit Board (PCB) requirements
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Load switch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Qui	ck reference data							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
Per transistor								
V _{CEO}	collector-emitter voltage	open base		-	-	-60	V	
I _C	collector current			-	-	-1	А	
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-1.5	А	
Per transistor								
R _{CEsat}	collector-emitter saturation resistance	I _C = -0.5 A; I _B = -50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C		-	-	360	mΩ	

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	6 5 4	C1 B2 E2
2	B1	base TR1		
3	C2	collector TR2	7 8	
4	E2	emitter TR2		
5	B2	base TR2		E1 B1 C2
6	C1	collector TR1	Transparent top view DFN2020-6 (SOT1118)	sym138
7	C1	collector TR1	2	
8	C2	collector TR2		

6. Ordering information

Table 3. Ordering information								
Type number	Package	Package						
	Name	Description	Version					
PBSS5160PAP	DFN2020-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body $2 \times 2 \times 0.65$ mm	SOT1118					

7. Marking

Table 4. Marking codes	
Type number	Marking code
PBSS5160PAP	2L

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transist	tor				
V _{CBO}	collector-base voltage	open emitter	-	-60	V
V _{CEO}	collector-emitter voltage	open base	-	-60	V
V _{EBO}	emitter-base voltage	open collector	-	-7	V
I _C	collector current		-	-1	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-1.5	А
IB	base current		-	-0.3	А
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Symbol	Parameter	Conditions	Mi	in Max	Unit
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms	-	-1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	370	mW
			[2] -	570	mW
			[3] -	530	mW
			[4] -	700	mW
			[5] -	450	mW
			[6] -	760	mW
			[7] -	700	mW
			[8] -	1450	mW
Per device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] -	510	mW
			[2] -	780	mW
			[3] -	730	mW
			[4] -	960	mW
			[5] -	620	mW
			[6] -	1040	mW
			[7] -	960	mW
			[8] -	2000	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-5	5 150	°C
T _{stg}	storage temperature		-6	5 150	°C

Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated and standard footprint.
 Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.

^[4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

[5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.

[6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm².

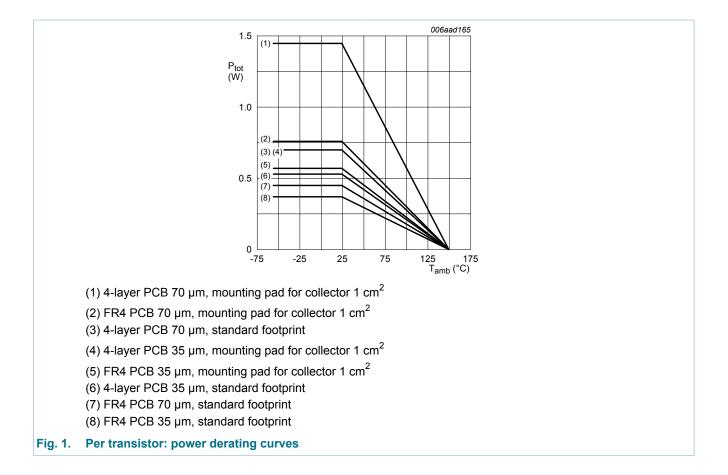
[7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.

[8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

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9. Thermal characteristics

Table 6. T	hermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per transist	tor			·			,
R _{th(j-a)}	thermal resistance	in free air	[1]	-	-	338	K/W
from junction to ambient			[2]	-	-	219	K/W
	ampient		[3]	-	-	236	K/W
			[4]	-	-	179	K/W
			[5]	-	-	278	K/W
			[6]	-	-	164	K/W
			[7]	-	-	179	K/W
			[8]	-	-	86	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	30	K/W

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Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per device							
ui(j-a)	thermal resistance	in free air	[1]	-	-	245	K/W
	from junction to		[2]	-	-	160	K/W
	ampient		[3]	-	-	171	K/W
			[4]	-	-	130	K/W
			[5]	-	-	202	K/W
			[6]	-	-	120	K/W
			[7]	-	-	130	K/W
			[8]	-	-	63	K/W

Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated and standard footprint.
 Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.

^[4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

[5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.

[6] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

[7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.

[8] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm².

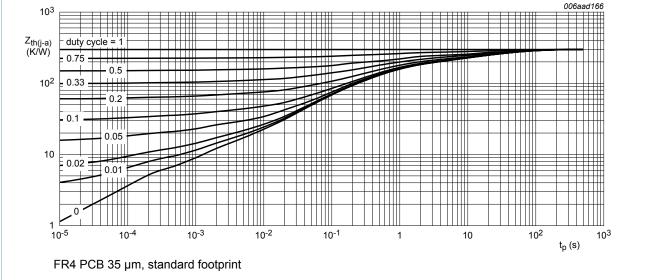
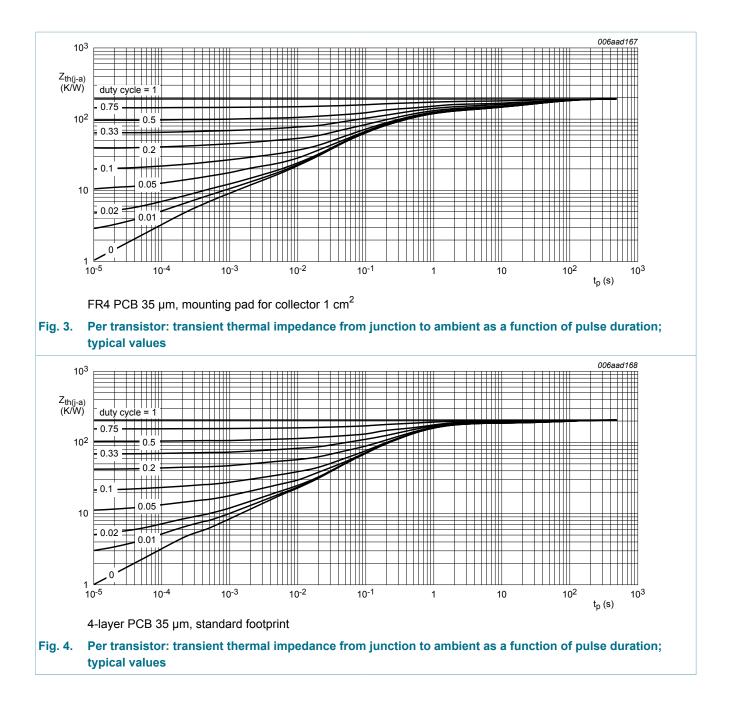


Fig. 2. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

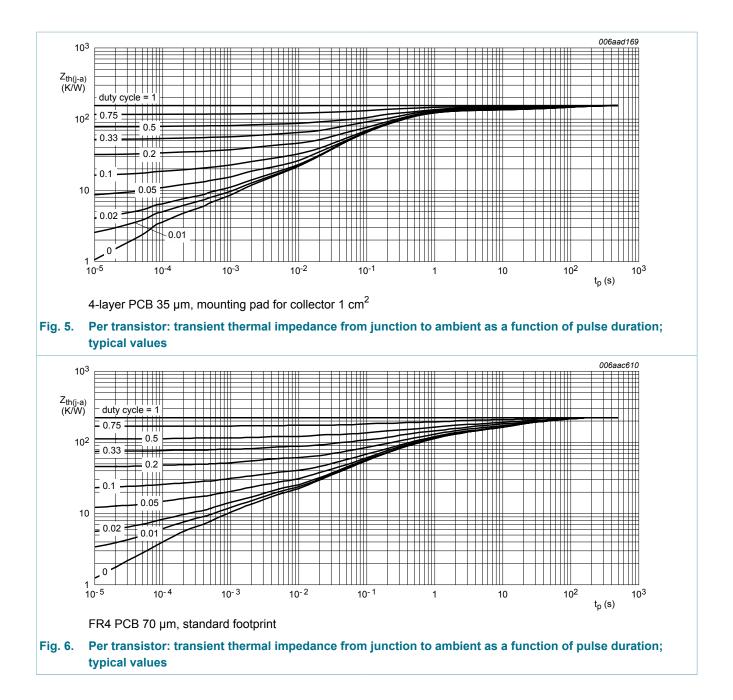


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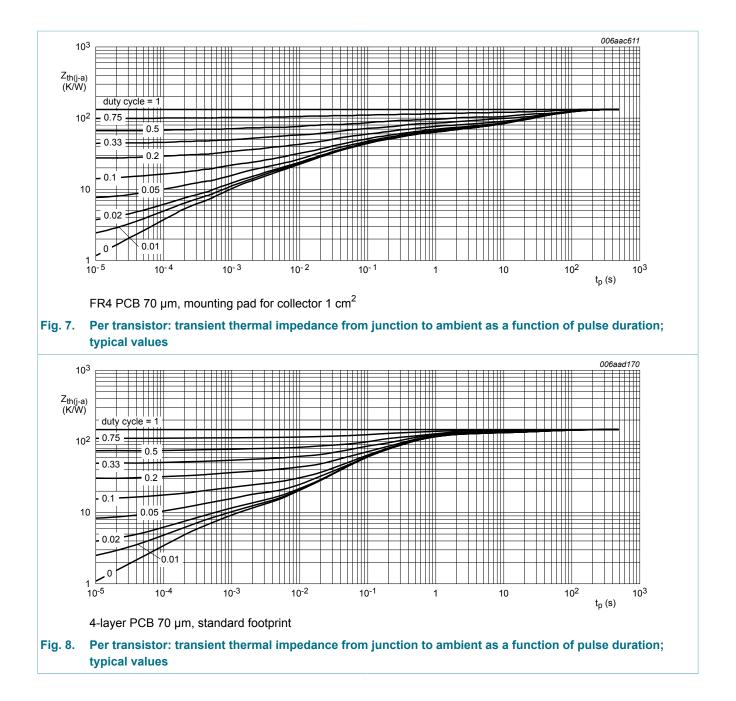


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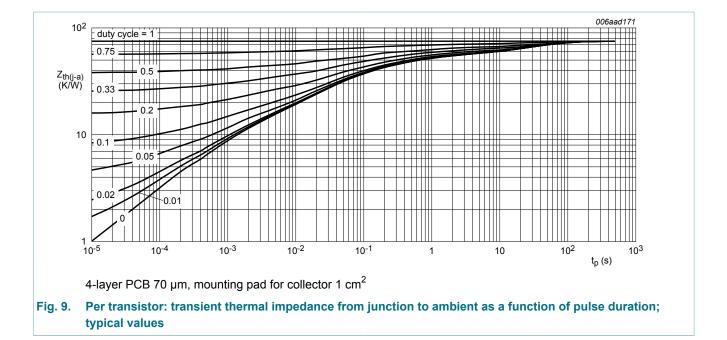


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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Per transist	tor					_
I _{CBO}	collector-base cut-off	V_{CB} = -48 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -48 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{EBO}	emitter-base cut-off current	V_{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	$\label{eq:V_CE} \begin{array}{l} V_{CE} = \text{-2 V; } I_{C} = \text{-100 mA; pulsed;} \\ t_{p} \leq 300 \ \mu s; \ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^{\circ}C \end{array}$	170	245	-	
		$\label{eq:VcE} \begin{array}{l} V_{CE} = \text{-2 V; } I_{C} = \text{-500 mA; pulsed;} \\ t_{p} \leq 300 \ \mu s; \ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^{\circ}C \end{array}$	120	170	-	
		$\label{eq:V_CE} \begin{array}{l} V_{CE} = \text{-2 V; } I_{C} = \text{-1 A; pulsed;} \\ t_{p} \leq 300 \ \mu s; \ \delta \leq 0.02 \ ; \ T_{amb} = 25 \ ^{\circ}C \end{array}$	70	100	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -500 mA; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-125	-180	mV
		I_{C} = -1 A; I_{B} = -50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-390	-550	mV
		I _C = -1 A; I _B = -100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-240	-340	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -0.5 A; I_{B} = -50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-	360	mΩ

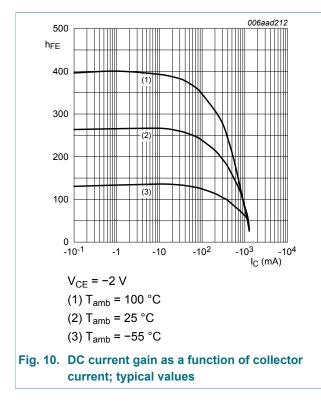
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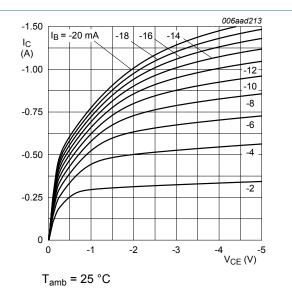
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{BEsat}	base-emitter saturation voltage	I_C = -500 mA; I_B = -50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-	-1	V
		I_{C} = -1 A; I_{B} = -50 mA; T_{amb} = 25 °C	-	-	-1	V
		$\begin{split} I_{C} &= -1 \text{ A}; \text{ I}_{B} = -100 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300 \mu\text{s}; \delta \leq 0.02 ; \text{T}_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-	-1.1	V
V _{BEon}	base-emitter turn-on voltage	$\label{eq:VcE} \begin{array}{l} V_{CE} \texttt{=} \texttt{-2} \; V; \; I_{C} \texttt{=} \texttt{-0.5} \; A; \; pulsed; \\ t_{p} \texttt{\leq} \texttt{300} \; \mu \texttt{s}; \; \delta \texttt{\leq} \texttt{0.02} \; ; \; T_{amb} \texttt{=} \texttt{25} \; ^{\circ} C \end{array}$	-	-	-0.9	V
t _d	delay time	V_{CC} = -10 V; I _C = -0.5 A; I _{Bon} = -25 mA; I _{Boff} = 25 mA; T _{amb} = 25 °C	-	15	-	ns
t _r	rise time		-	40	-	ns
t _{on}	turn-on time		-	55	-	ns
ts	storage time		-	95	-	ns
t _f	fall time		-	40	-	ns
t _{off}	turn-off time		-	135	-	ns
f _T	transition frequency	V_{CE} = -10 V; I _C = -50 mA; f = 100 MHz; T _{amb} = 25 °C	65	125	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	9.5	13	pF







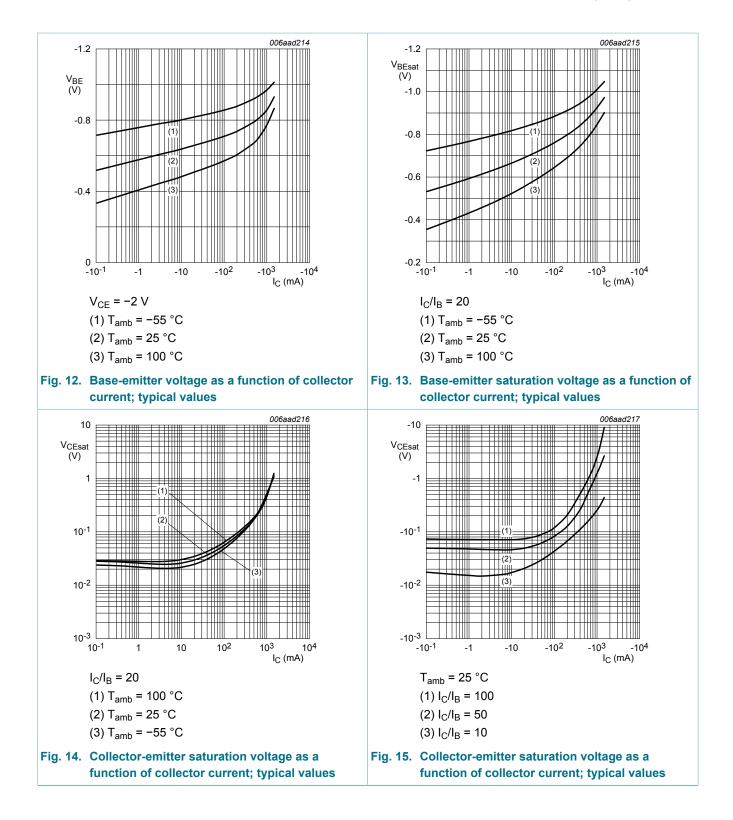
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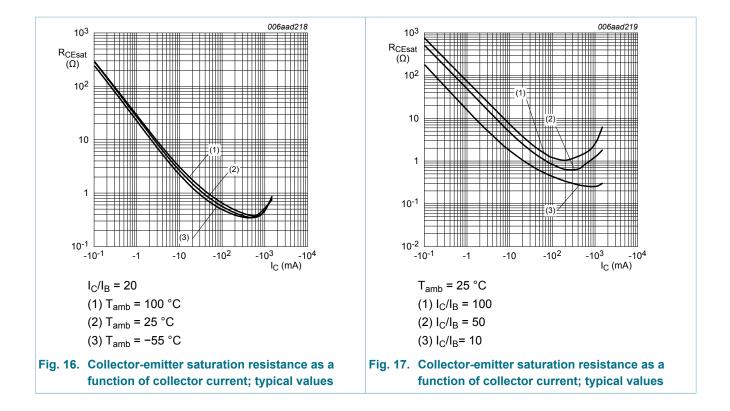


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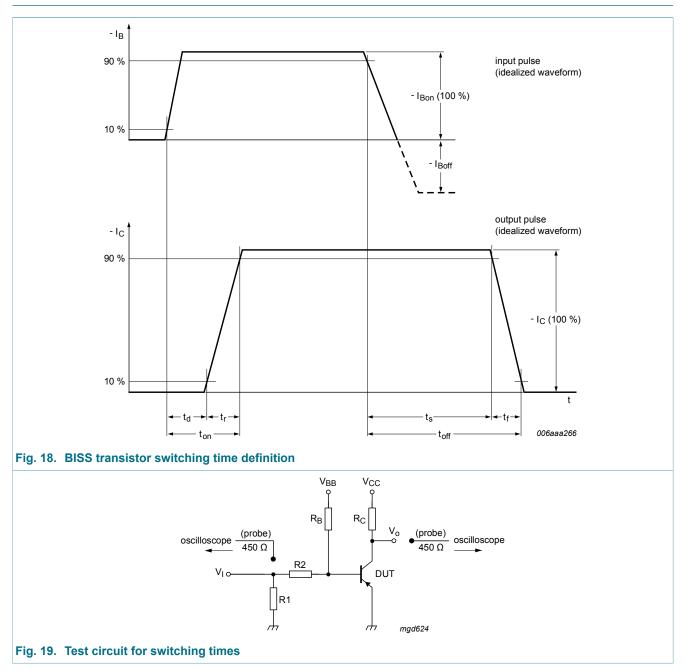
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11. Test information



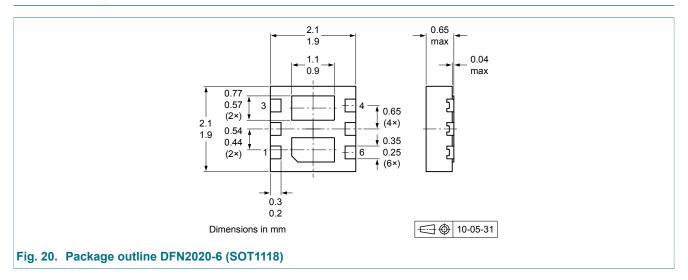
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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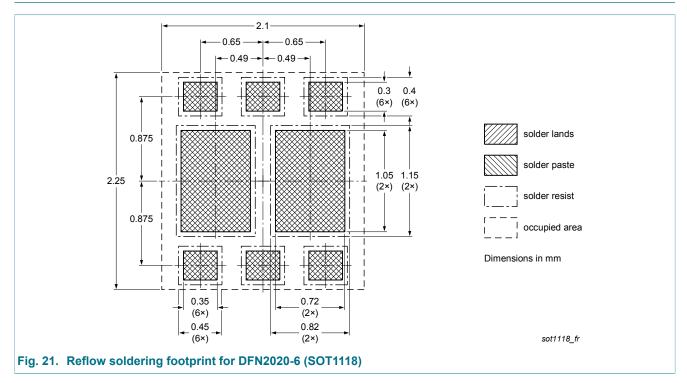
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12. Package outline



13. Soldering



14. Revision history

Table 8. Revision hi	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5160PAP v.1	20130123	Product data sheet	-	-
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Product data sheet		23 January 2013		14 / 17

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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